TOSHIBA TRANSISTOR SILICON NPN PLANAR TYPE

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UHF TV TUNER RF AMPLIFIER APPLICATIONS

• Low Noise Figure : NF=2.8dB (Typ.)

 $\bullet \qquad \text{High Power Gain V}_{CC} \!=\! 4.5 \text{V} \ : G_{pb} \!=\! 15 \text{dB (Typ.)}$

• Excellent Forward AGC Characteristics

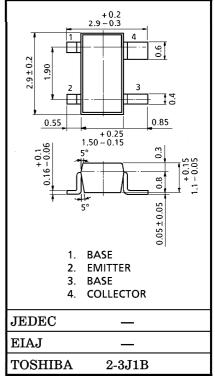
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	25	V
Collector-Emitter Voltage	v_{CEO}	20	V
Emitter-Base Voltage	$V_{ m EBO}$	2	V
Base Current	I_{B}	4	mA
Collector Current	$I_{\mathbf{C}}$	20	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	150	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

Marking



Unit in mm

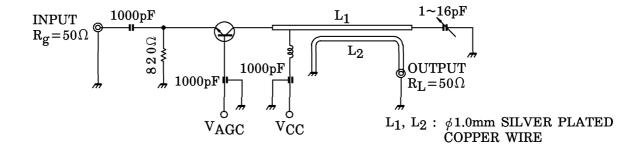


Weight: 0.013g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

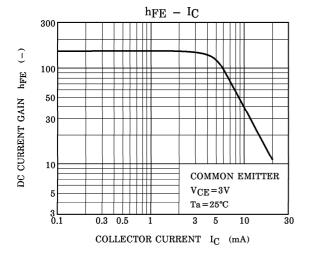
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 10V, I_{E} = 0$	_	_	0.1	μ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB}=2V, I_{C}=0$	_	_	1	μ A
Collector Emitter Breakdown Voltage	V _(BR) CEO	$I_{C}=1$ mA, $I_{B}=0$	20	_	_	V
DC Current Gain	$h_{ ext{FE}}$	V_{CE} =3.0V, I_{C} =1mA	40	100	_	_
Transition Frequency	$f_{ m T}$	V_{CE} =3.0V, I_{C} =1mA	500	850	_	MHz
Reverse Transfer Capacitance	$\mathrm{C_{rb}}$	$V_{CE} = 2.0V, I_{B} = 0, f = 1MHz$	_	0.3	0.5	pF
Power Gain	$G_{ m pb}$	$V_{CC}=4.5V$, $V_{AGC}=2.0V$	10	15	_	dB
Noise Figure	NF	f=800MHz (Fig.1)	_	2.8	4.5	dB
AGC Voltage	VAGC	V _{CC} =4.5V, G.R.=-20dB f=800MHz	2.5	3.2	4.0	V

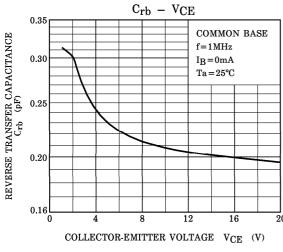
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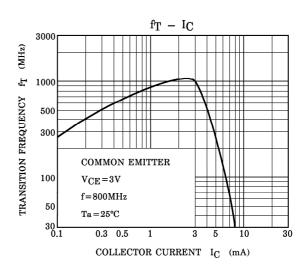


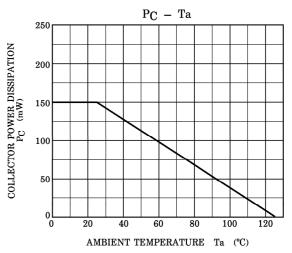
(Note) VAGC measured by the test circuit shown in Fig.1, when the power gain is reduced to 20dB compared with Gpb shown above Table.

Fig.1 800MHz Gpb, NF TEST CIRCUIT

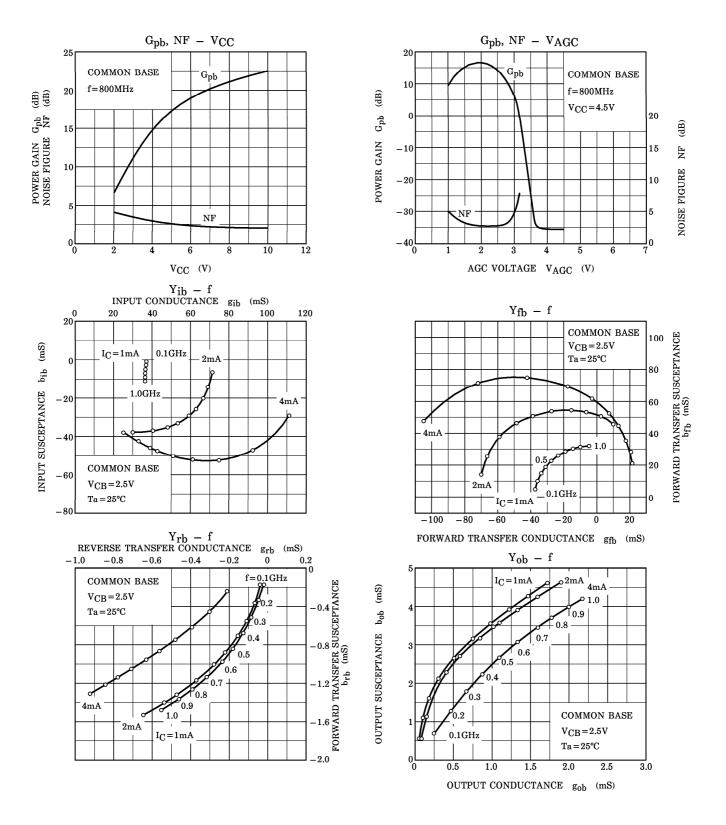








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